





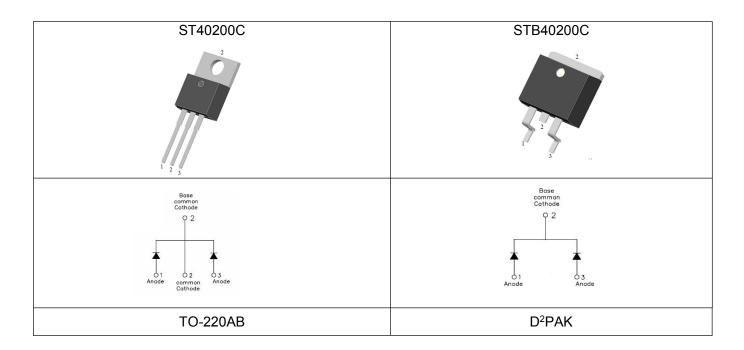
# ST40200C/STB40200C SCHOTTKY RECTIFIER

## **Applications**

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

### **Features**

- 150 °C T<sub>J</sub> operation
- Ultralow forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Trench MOS Schottky technology
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request



# **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	200	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @Tc=100°C, rectangular wave form	20(Per Leg) 40(Per Device)	Α
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I <sub>FSM</sub>	8.3ms, Half Sine pulse	250	Α

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## **Electrical Characteristics:**

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop(Per Leg)*	V <sub>F1</sub>	@ 20A, Pulse, T <sub>J</sub> = 25 °C	-	1.60	V
	V <sub>F2</sub>	@ 20A, Pulse, T <sub>J</sub> = 125 °C	-	0.76	V
Reverse Current(Per Leg)*	I <sub>R1</sub>	$@V_R = \text{rated } V_R$ $T_J = 25  ^{\circ}\text{C}$	-	0.3	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R$ $T_J = 125  ^{\circ}\text{C}$	-	36	mA

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

## **Thermal-Mechanical Specifications:**

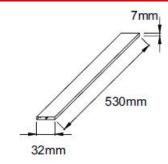
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +150	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +150	°C
Typical Thermal Resistance Junction to Case(Per Leg)	R <sub>θJC</sub>	DC operation	1.8	°C/W

## **Tube Specification**

Device	Package	Weight	Shipping
ST40200C	TO-220AB	2.0	50pcs / tube
STB40200C	D² PAK	1.85	800pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

# **Tube Specification(TO-220AB)**



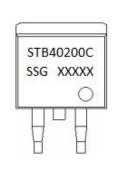






## **Marking Diagram**



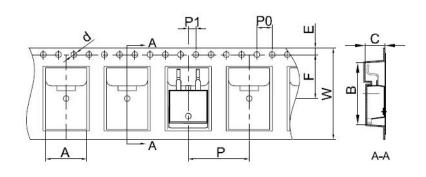


#### Where XXXXX is YYWWL

ST = Device Type
B = Package type
40 = Forward Current (40A)
200 = Reverse Voltage (200V)
C = Configuration

**Cautions:** Molding resin Epoxy resin UL:94V-0

## **Carrier Tape Specification D2PAK**



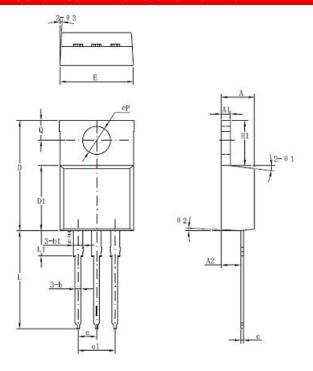
SYMBOL	Millimeters		
STWIBOL	Min.	Max.	
Α	10.70	10.90	
В	16.03	16.23	
С	5.11	5.31	
d	1.45	1.65	
E	1.65	1.85	
F	11.40	11.60	
P0	3.90	4.10	
Р	15.90	16.10	
P1	1.90	2.10	
W	23.90	24.30	





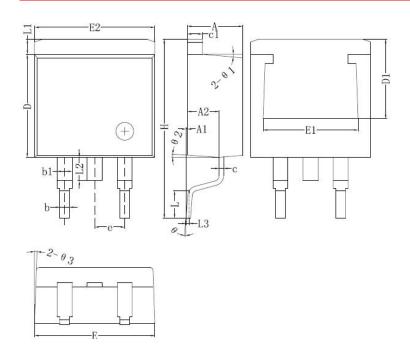


## **Mechanical Dimensions TO-220AB**



Symbol	Dimensions in millimeters			
	Min	Typical	Max	
Α	4.42	4.57	4.72	
A1	1.17	1.27	1.37	
A2	2.52	2.69	2.89	
b	0.71	0.81	0.96	
b1	1.17	1.27	1.37	
С	0.31	0.38	0.61	
D	14.94	15.24	15.54	
D1	8.85	9.00	9.15	
E	10.01	10.16	10.31	
е		2.54		
e1	4.98	5.06	5.18	
H1	6.04	6.24	6.44	
L	12.7	13.56	13.80	
L1	3.56	3.5	3.96	
ФР	3.74	3.84	4.04	
Q	2.54	2.74	2.94	
Θ1		7°		
Θ2		3°		
Θ3		4°		

## **Mechanical Dimensions D<sup>2</sup>PAK**



Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
Α	4.47	4.70	4.85
A1	0	0.10	0.25
A2	2.59	2.69	2.89
b	0.71	0.81	0.96
b1	1.17	1.27	1.37
С	0.31	0.38	0.61
c1	1.17	1.27	1.37
D	8.50	8.70	8.90
D1	6.40		
E	10.01	10.16	10.31
E1	7.6		
E2	9.98	10.08	10.31
е		2.54	
Н	14.6	15.1	15.6
L	2.00	2.30	2.74
L1	1.12	1.27	1.42
L2	1.30		2.20
L3		0.25BSC	
е	0	-	8°
e1		5°	
e2		4°	
e3		4°	

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